

BOX PCT

IN THE UNITED STATES ELECTED/DESIGNATED OFFICE  
OF THE UNITED STATES PATENT AND TRADEMARK OFFICE  
UNDER THE PATENT COOPERATION TREATY-CHAPTER II

APPLICANTS: Okuyama et al.  
SERIAL NO:

DOCKET NO: 113278-006  
GROUP ART UNIT:  
EXAMINER:

INTERNATIONAL APPLICATION NO: PCT/JP01/06214

INTERNATIONAL FILING DATE: 18 July 2001

INVENTION: SEMICONDUCTOR LIGHT-EMITTING ELEMENT AND  
SEMICONDUCTOR LIGHT-EMITTING DEVICE

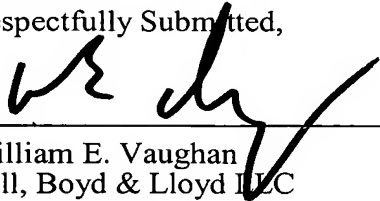
Assistant Commissioner for Patents,  
Washington, D.C. 20231

**INFORMATION DISCLOSURE STATEMENT**

In accordance with the provisions of 37 CFR §1.56, Applicants request that citation and examination of the references listed on Form PTO-1449, copies of which are enclosed herewith in accordance with 37 CFR §1.98, be made during the course of examination of the above-identified application for United States Patent.

Accordingly, early consideration and allowance of the application, including the claims, are hereby requested.

Respectfully Submitted,

  
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PCT/JP01/06214

Sheet 1 of 1

37 CFR 1.501 INFORMATION DISCLOSURE STATEMENT IN A PATENT (use several sheets if necessary)						Docket No. 113278-006		Serial No.	
						Applicant: Okuyama et al..			
						Filing Date		Group Art Unit	
<b>U.S. PATENT DOCUMENTS</b>									
Examiner's Initials	AA	Document Number	Date	Name	Class	Subclass	Filing Date If appropriate		
	AB								
	AC								
	AD								
	AE								
	AF								
	AG								
	AH								
	AI								
	AJ								
	AK								
<b>FOREIGN PATENT DOCUMENTS</b>									
		Document Number	Date	Country	Class	Subclass	Translation		
	AL	5-251738	9-28-93	Japan			Yes	No	
	AM								
	AN								
	AO								
	AP								
	AQ								
	AR								
	AS								
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>									
		K. Tachibana et al., "Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature" Applied Physics Letters, 29 May 2000, Vol. 76, No. 22, pages 3212-3214							
		D. Kapolnek et al., "Spatial control of InGaN luminescence by MOCVD selective epitaxy" Journal of Crystal Growth, (1998), Vol. 189/190, pages 83-86							
Examiner				Date Considered					
<b>*EXAMINER:</b> Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									